

## GaAs PIN PHOTODIODES

## PD-8150 Series

### PIN Photodiode with Mini-Size TO Package

#### FEATURES

- 2 High Responsivity for 850 nm
- 2 Low Dark Current
- 2 Quick Pulse Response
- 2 **2.4 mm Mini-Size Package**
- 2 Active Diameter 100  $\mu$  m

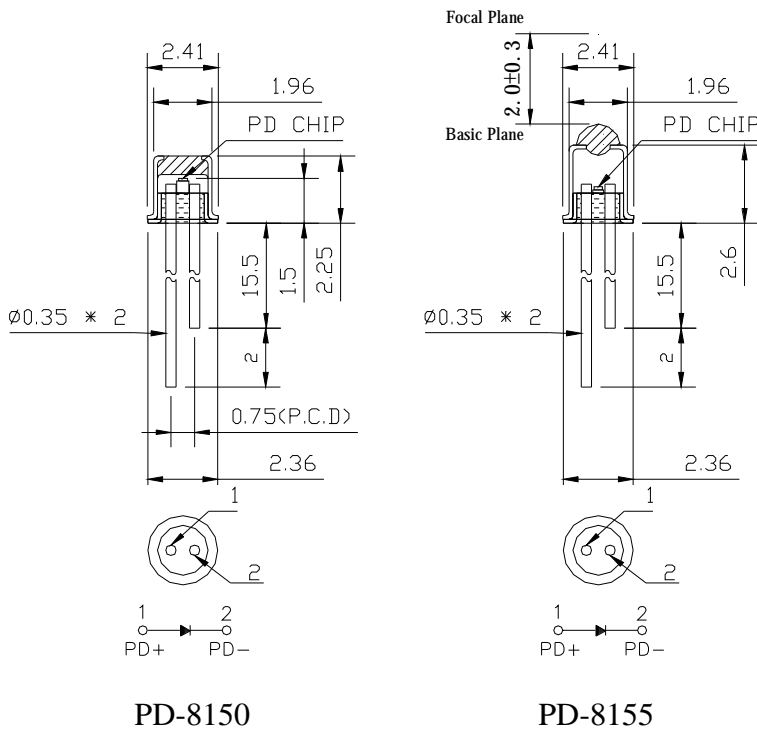
#### DESCRIPTION

PD-8150 series InGaAs Photodiode are suited to receive the light at the wavelength range from 600 nm to 1000 nm. With high reliability, PD-8150 series are the best choice for datacom application.

<b>PD-8160-100 ELECTRICAL AND OPTICAL CHARACTERISTICS (T<sub>C</sub>=25°C)</b>						
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
	Active Area			100		$\mu$ m
	Detection Range		600		1000	nm
R	Responsivity	V <sub>R</sub> =5V, $\lambda$ =850nm	0.45	0.5	-	A/W
I <sub>dark</sub>	Dark Current	V <sub>R</sub> =5V			0.5	nA
C	Capacitance	V <sub>R</sub> =5V			0.7	pF
T <sub>r</sub> /T <sub>f</sub>	Rise/Fall Time	V <sub>R</sub> =5V, 10~90%			0.3	ns
BW	Bandwidth	V <sub>R</sub> =5V	2			GHz

<b>ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub>=25 °C)</b>			
Symbol	Parameter	Ratings	Unit
P <sub>o</sub>	Input Optical Power	10	mW
V <sub>RD</sub>	Reverse Voltage	20	V
I <sub>FD</sub>	Forward Current	10	mA
T <sub>opr</sub>	Operating Temperature	-40~+85	°C
T <sub>stg</sub>	Storage Temperature	-40~+85	°C

MECHANICAL DIMENSION (mm) and PIN ASSIGNMENT



ORDER INFORMATION

Part No.: P D - 8 1 5  -

Code	Cap
0	Flat Window
5	Ball lens

Code	Chip Diameter
100	100 μm